

Title (en)

METHOD FOR PRODUCING AN INTEGRATED CIRCUIT PROCESSED ON BOTH SIDES

Title (de)

VERFAHREN ZUR HERSTELLUNG EINES BEIDSEITIG PROZESSIERTEN INTEGRIERTEN SCHALTKREISES

Title (fr)

PROCEDE DE PRODUCTION D'UN CIRCUIT INTEGRE TRAITE SUR SES DEUX FACES

Publication

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Application

EP 99956002 A 19991117

Priority

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- EP 9908817 W 19991117

Abstract (en)

[origin: DE19853703A1] IC production comprises applying a metallization onto a thinned finished wafer bonded to a handling wafer for connection by vias to the finished wafer metallization (2, 3) and/or circuit structure (1). An IC production process comprises providing via holes to the back face of a first substrate having a circuit structure (1) and an overlying metallization structure (2, 3), insulating the via holes from the circuit structure, applying a planarizing layer over the metallization structure, bonding the resulting first wafer to a handling wafer, thinning the first wafer from the back face to expose the via holes or their metallized connections and applying a second metallization structure on the chip back face for connection by the vias with the first metallization structure and/or the circuit structure. Independent claims are also included for the following: (i) an IC produced by the above process; (ii) a module for incorporation in a chip card, the module comprising the above IC; and (iii) a chip card having the above IC or module.

IPC 1-7

H01L 23/48; **H01L 23/528**

IPC 8 full level

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Citation (search report)

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